

PRELIMINARY DATA SHEET: CA3508M4

L TO S BAND LOW NOISE AMPLIFIER

Features :

- Low noise figure and high associated gain
NF=0.43dB Typ., Ga=18.0dB Typ.
@Vdd=3.0V, Idd=30mA, f=1.575GHz

Description :

- Low Noise and High Gain
- On chip Bias supply circuit
- On chip ESD protection diode

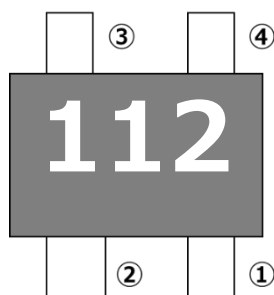
Applications :

- LNA IC for GNSS/4K,8K LNA Block

Package :

- Flat-lead 4-pin thin-type super minimold package

PIN Configuration :



PIN No.	PIN Name
1	Source
2	OUT
3	Source
4	IN

Ordering Information :

Part Number	Order Number	Package	Marking	Supplying Form
CA3508M4-C2	CA3508M4-C2	Flat-lead 4-pin thin-type super minimold package	112	<ul style="list-style-type: none"> • Embossed 8 mm wide • Pin 1 (Source), Pin 2 (OUT) • Face the perforation side of the Tape • Qty 15Kpcs/reel

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Absolute Maximum Ratings :

Parameter	Symbol	Rating	Unit
Supply Voltage	Vdd	4.0	V
Input Power	Pin	+13	dBm
Operating Ambient Temperature	T _A	-45~+85	°C
Storage Temperature	Tstg	-55~+150	°C

Recommended Operating Range :

(T_A=+25°C, unless otherwise specified)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	Vdd	2.7	3.0	3.3	V
Supply Current	Idd	TBD	30	TBD	mA

Electrical Characteristics :

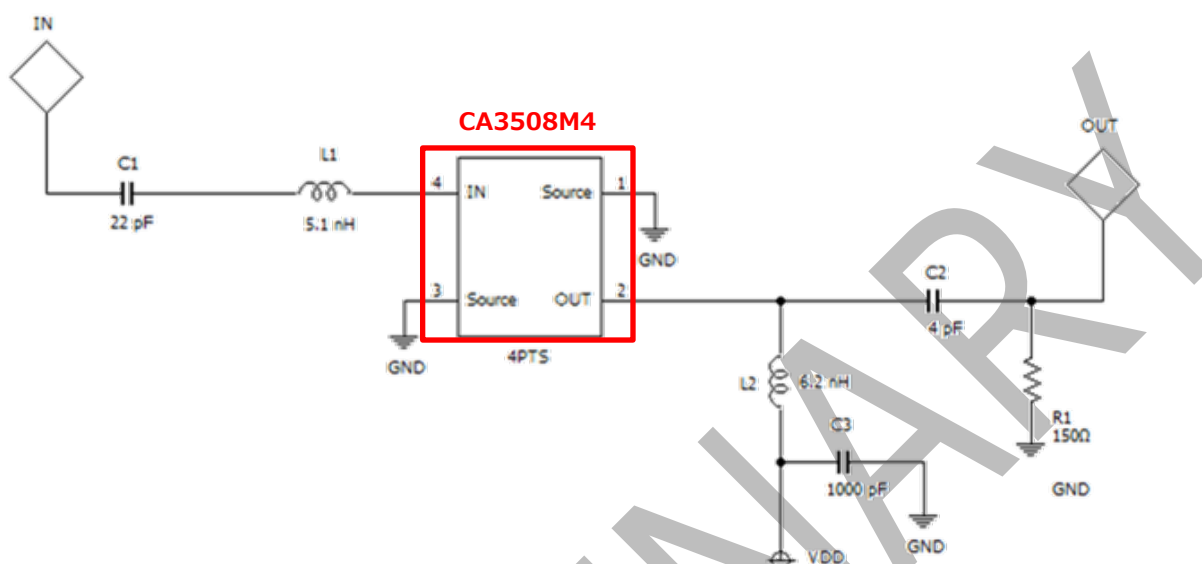
(T_A=+25°C, unless otherwise specified)

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Power Gain	Gain	Vdd=3.0V, Idd=30mA, f=1.575GHz	TBD	18.0	-	dB
Noise Figure	NF	f=1.575GHz	-	0.43	TBD	dB
Input 3rd Order Intercept Point	IIP3	Vdd=3.0V, Idd=30mA, f=1.575GHz	-	TBD	-	dBm
Output Power at 1dB Compression Point	P _{O(1dB)}	Vdd=3.0V, Idd=30mA (Non-RF) f=1.575GHz	-	12.0	-	dBm

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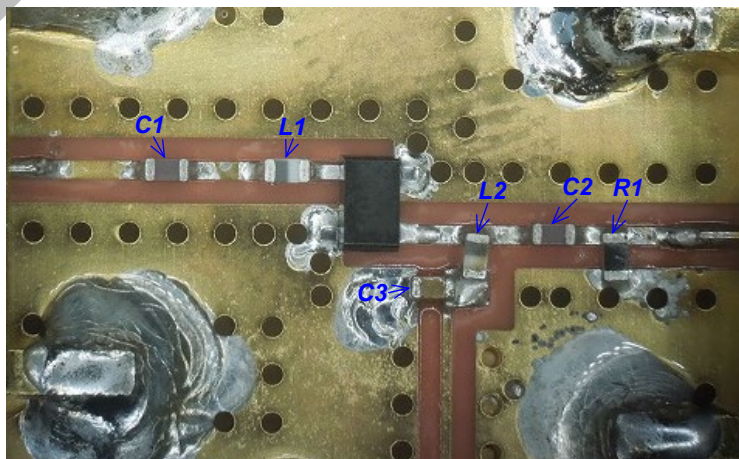
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Application Circuit:



Evaluation Board Information :

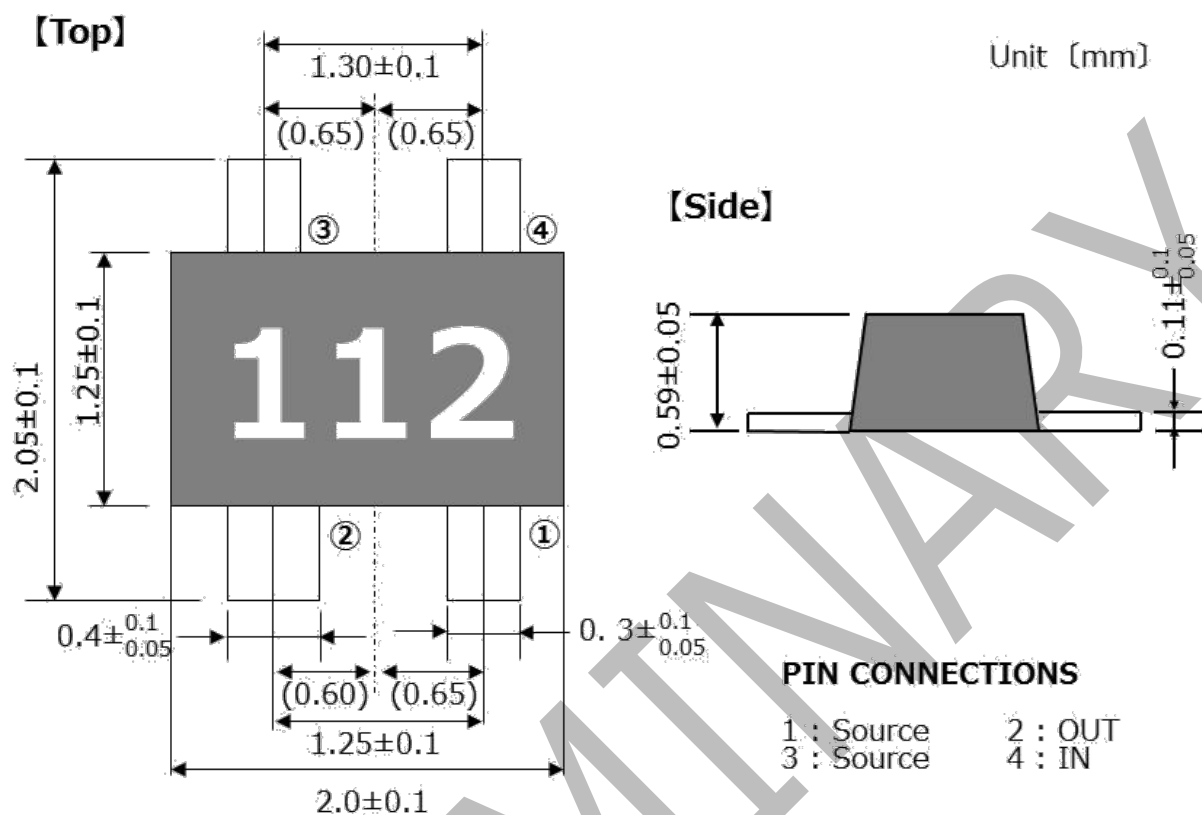
<PCB>
 FR-4
 t = 0.2 mm
 $\epsilon_r = 4.30$
 $\tan \delta = 0.016$



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Package Dimensions :





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[Caution in the gallium arsenide (GaAs) product handling]

This product uses gallium arsenide (GaAs) of the toxic substance appointed in laws and ordinances. GaAs vapor and powder are hazardous to human health if inhaled or ingested.

- Do not dispose in fire or break up this product.
- Do not chemically make gas or powder with this product.
- When discard this product, please obey the law of your country.
- Do not lick the product or in any way allow it to enter the mouth.

[CAUTION]

Although this device is designed to be as robust as possible, ESD (Electrostatic Discharge) can damage this device. This device must be protected at all times from ESD. Static charges may easily produce potentials of several kilovolts on the human body or equipment, which can discharge without detection. Industry-standard ESD precautions should be used at all times.

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For a complete list of sales offices, representatives and distributors,

Please visit our website: www.cel.com/contactus

For inquiries email us at r fw@cel.com



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Revision History

Version	Change to current version	Page(s)
CDS-0058-01 Sept. 2018	Preliminary data sheet	N/A